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PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known

Application Number	09/904,906
Filing Date	July 16, 2001
First Named Inventor	Takeshi FUKADA et al.
Group Art Unit	2825
Examiner Name	L. Malsawma
Attorney Docket Number	0756-2332

Sheet

1

of

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U.S. PATENT DOCUMENTS

Examiner Initials [*]	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
JLM		4,416,952		Nishizawa et al.	11/22/1983	
		4,727,044		Yamazaki	02/23/1988	
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Examiner Initials [*]	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
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JLM		JP	03-024736			02/01/1991		AB

Examiner Signature

Mail JLM for Lex Malsawma

Date Considered

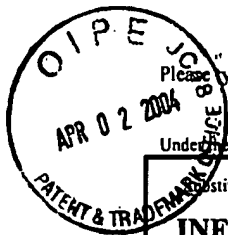
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Sheet	2	of	2	Attorney Docket Number	0756-2332

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Alm		Gang Liu et al., <i>Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing</i> , Appl. Phys. Lett., Vol. 62, No. 20, Pages 2554-2556, May 17, 1993.	
Alm		Gang Liu et al., <i>Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing</i> , Appl. Phys. Lett., Vol. 55, No. 7, Pages 660-662, August 14, 1989.	
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Examiner Signature	<i>Alm</i>	Date Considered	6/12/2004
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